RoHS

COMPLIANT

BYV26DGP & BYV26EGP

Vishay General Semiconductor

Glass Passivated Ultrafast Rectifier



PRIMARY CHARACTERISTICS				
I _{F(AV)}	1.0 A			
V _{RRM}	800 V, 1000 V			
I _{FSM}	30 A			
t _{rr}	75 ns			
V _F	1.3 V			
T _J max.	175 °C			
Hont	29 A 2 A 2 A A			

FEATURES

- Cavity-free glass-passivated junction
- Ultrafast reverse recovery time
- · Low forward voltage drop
- Low switching losses, high efficiency
- High forward surge capability
- Meets environmental standard MIL-S-19500
- Solder dip 260 °C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

TYPICAL APPLICATIONS

For use in high frequency rectification and freewheeling application in switching mode converters and inverters for consumer, computer and telecommunication.

MECHANICAL DATA

Case: DO-204AC, molded epoxy over glass body Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test, HE3 suffix for high reliability grade (AEC Q101 qualified), meets JESD 201 class 2 whisker test

Polarity: Color band denotes cathode end

MAXIMUM RATINGS ($T_A = 25 \text{ °C}$ unless otherwise noted)					
PARAMETER	SYMBOL BYV26DGP BYV26EGP		UNIT		
Maximum repetitive peak reverse voltage	V _{RRM}	800	1000	V	
Maximum RMS voltage	V _{RMS}	560	700	V	
Maximum DC blocking voltage	V _{DC}	800 1000		V	
Maximum average forward rectified current 0.375" (9.5 mm) lead length (Fig. 1)	I _{F(AV)}	1.0		А	
Peak forward surge current 10 ms single half sine-wave superimposed on rated load	I _{FSM}	30		А	
Non repetitive peak reverse energy (1)	E _{RSM}	10		mj	
Operating junction and storage temperature range	T _J , T _{STG}	- 65 to + 175		°C	

Note:

(1) Peak reverse energy measured at I_R = 400 mA, T_J = T_J max. on inductive load, t = 20 μ s

Document Number: 88554 Revision: 20-Aug-07 For technical questions within your region, please contact one of the following: PDD-Americas@vishay.com, PDD-Asia@vishay.com, PDD-Europe@vishay.com

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ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	BYV26DGP	BYV26EGP	UNIT
Minimum avalanche breakdown voltage	100 µA		V _{BR}	900 1100		V
Maximum instantaneous forward voltage	1.0 A	T _J = 25 °C T _J = 175 °C	V _F	2.5 1.3		v
Maximum DC reverse current at rated DC blocking voltage		T _A = 25 °C T _A = 165 °C	I _R	5.0 150		μΑ
Max. reverse recovery time	I _F = 0.5 A, I _R = 1.0 A, I _{rr} = 0.25 A		t _{rr}	75		ns
Typical junction capacitance	4.0 V, 1 M	Hz	CJ	15		pF

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	BYV26DGP	BYV26EGP	UNIT	
Typical thermal resistance ⁽¹⁾⁽²⁾	R _{θJA} R _{θJL}	70 16		°C/W	

Notes:

(1) Thermal resistance from junction to ambient at 0.375" (9.5 mm) lead length, mounted on P.C.B. with 0.5 x 0.5" (12 x 12 mm) copper pads

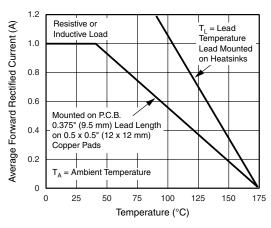
(2) Thermal resistance from junction to lead at 0.375" (9.5 mm) lead length with both leads attached to heatsink

ORDERING INFORMATION (Example)						
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
BYV26EGP-E3/54	0.428	54	4000	13" diameter paper tape and reel		
BYV26EGP-E3/73	0.428	73	2000	Ammo pack packaging		
BYV26EGPHE3/54 (1)	0.428	54	4000	13" diameter paper tape and reel		
BYV26EGPHE3/73 ⁽¹⁾	0.428	73	2000	Ammo pack packaging		
Note: DIECEI UTILLE D.A. LE C.F.						

(1) Automotive grade AEC Q101 qualified

RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)





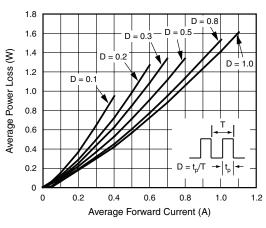


Figure 2. Forward Power Loss Characteristics

Document Number: 88554 Revision: 20-Aug-07

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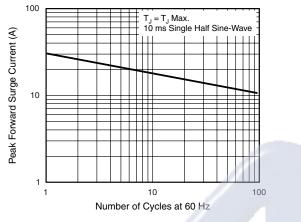


Figure 3. Maximum Non-Repetitive Peak Forward Surge Current

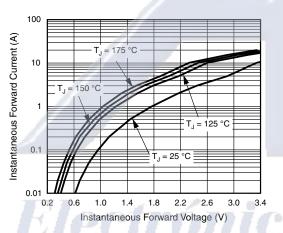


Figure 4. Typical Instantaneous Forward Voltage Characteristics

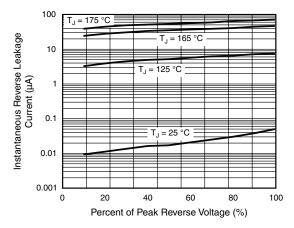


Figure 5. Typical Reverse Leakage Characteristics

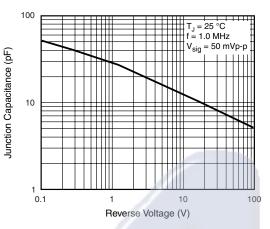
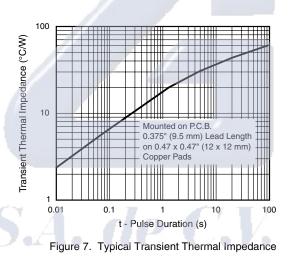


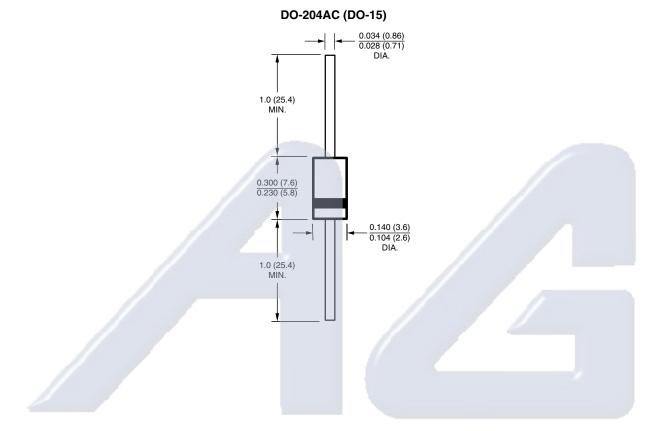
Figure 6. Typical Junction Capacitance



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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)



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4

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